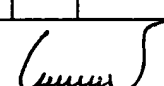
		Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KM1-001		SERIAL NO. 09/652,550			
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)						APPLICANT: Keiji Jono et al.			
								FILING DATE August 31, 2000		GROUP 2811	
U.S. PATENT DOCUMENTS											
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate					
qv	AA	6,034,409	03/07/2000	Sakai et al.							
qv	AB	6,171,924 B1	01/09/2001	Wang et al.							
qv	AC	6,154,417	11/28/2000	Kim							
	AD										
	AE										
	AF										
	AG										
	AH										
	AI										
	AJ										
	AK										
FOREIGN PATENT DOCUMENTS											
	Document Number	Date	Country	Class	Subclass	Translation					
						Yes	No				
	AL										
	AM										
	AN										
	AO										
	AP										
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)											
AR											
AS											
AT											
EXAMINER				DATE CONSIDERED							
				08/14/03							
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.											

Form PTO-1279 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KMI-001		SERIAL NO.		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Keiji Jono et al.		
FILING DATE				GROUP		
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
FOREIGN PATENT DOCUMENTS						
Document Number	Date	Country	Class	Subclass	Translation	
					Yes	No
AL						
AM						
AN						
AO						
AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
9V	AR		Shallow Trench Isolation Characteristics with High-Density-Plasma Chemical Vapor Deposition Gap-Fill Oxide for Deep-Submicron CMOS			
			Technologies, Seung-Ho Lee et al., Jpn. J. Appl. Phys. Vol. 37 (1998), pp. 1222-1227.			
9V	AS		Impact of Shallow Trench Isolation on Reliability of Buried- and Surface-Chanel sub- μ m PFET, William Tonit et al., 1995 IEEE. pp. 24-29.			
9V	AT		Subbreakdown Drain Leakage Current in MOSFET, J. Chen et al., 1987 IEEE, pp.515-517.			
EXAMINER <i>Cumun</i>			DATE CONSIDERED 08/14/03			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

RECEIVED

TECHNOLOGY CENTER

JUN 18 2003

8800

Form 10-44P U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KM1-001		SERIAL NO.	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Keiji Jono et al.	
FILING DATE				GROUP	

JUN 12 2003
 PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation No		
AL							
AM							
AN							
AO							
AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
9v	AR	Shallow Trench Isolation for advanced ULSI CMOS Technologies, M. Nandakumar et al, Silicon Technology Development, Kilby Center, Texas Instruments, Undated, 4 pages.
	AS	
	AT	

EXAMINER Cunnu	DATE CONSIDERED 08/14/03
---	---

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.